TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

2 S C 2 7 0 3

AUDIO POWER AMPLIFIER APPLICATIONS.

• High DC Current Gain: hFE=100~320

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	v_{CBO}	30	V
Collector-Emitter Voltage	v_{CEO}	30	V
Emitter-Base Voltage	v_{EBO}	5	V
Collector Current	$I_{\mathbf{C}}$	1	Α
Base Current	I_{B}	0.1	Α
Collector Power Dissipation	$P_{\mathbf{C}}$	900	mW
Junction Temperature	T_{j}	150	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~150	°C

Unit in mm

5.1MAX.

0.75MAX.

1.8MAX.

0.6MAX.

1.8MIX TO SHITTER

2. COLLECTOR

3. BASE

JEDEC TO-92MOD

EIAJ —

TOSHIBA 2-5J1A

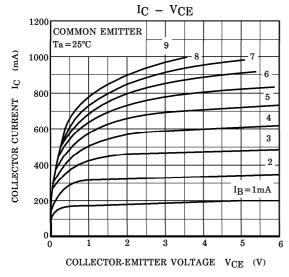
Weight: 0.36g

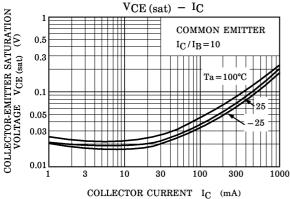
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

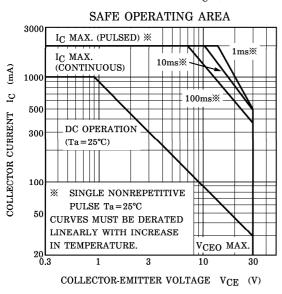
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	ICBO	$V_{CB} = 30V, I_{E} = 0$	_	_	100	nA
Emitter Cut-off Current	I _{EBO}	$V_{EB}=5V, I_{C}=0$	-	_	100	nA
Collector-Emitter Breakdown Voltage	V (BR) CEO	$I_{\rm C}=10{\rm mA},~I_{\rm B}=0$	30	_	_	V
DC Current Gain	hFE (1) (Note)	V _{CE} =2V, I _C =100mA	100	_	320	
	hFE (2)	$V_{CE} = 2V, I_{C} = 800 \text{mA}$	40	_	_	
Collector-Emitter Saturation Voltage	V _{CE} (sat)	I _C =800mA, I _B =80mA	_	_	0.5	V
Base-Emitter Voltage	$V_{ m BE}$	$V_{CE} = 2V, I_{C} = 800 \text{mA}$	_	0.9	1.5	V
Transition Frequency	$ m f_{T}$	$V_{CE} = 2V, I_{C} = 100 \text{mA}$	_	150	_	MHz
Collector Output Capacitance	C _{ob}	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$	_	13	_	pF

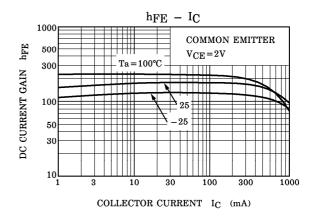
Note: $h_{FE(1)}$ Classification $O: 100\sim200, Y: 160\sim320$

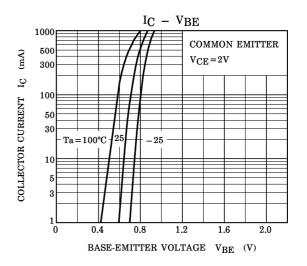
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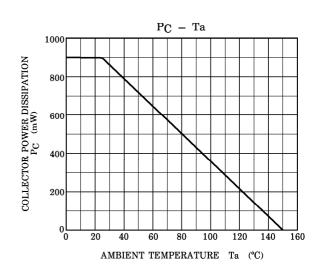












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